

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A semiconductor device comprising:
a conductive barrier film; and
a wiring containing Cu as its main component over the conductive barrier film,
wherein a width of a top surface of the conductive barrier film is not aligned with
that of the wiring containing Cu as its main component, and
wherein the width of the conductive barrier film is 30 to 40 μm and the width of
the wiring containing Cu as its main component is 5 to 20 μm .

2. (Previously Presented) A semiconductor device comprising:
a conductive barrier film; and
a wiring containing Cu as its main component over the conductive barrier film,
wherein a width of a top surface of the conductive barrier film is not aligned with
that of the wiring containing Cu as its main component,
wherein an insulating barrier film covers the top surface and a side surface of the
wiring containing Cu as its main component, and
wherein the width of the conductive barrier film is 30 to 40 μm and the width of
the wiring containing Cu as its main component is 5 to 20 μm .

3. (Previously Presented) A semiconductor device comprising:
a conductive film;
a conductive barrier film on the conductive film; and
a wiring containing Cu as its main component over the conductive barrier film,
wherein a width of the conductive film is aligned with that of the conductive

barrier film, and

wherein a width of the wiring containing Cu as its main component is narrower than that of the conductive barrier film.

4. (Previously Presented) A display device comprising:

at least a signal line and a scan line provided to intersect with the signal line,

wherein the signal line comprises a conductive film, a conductive barrier film on the conductive film, and a wiring containing Cu as its main component over the conductive barrier film, and

wherein a width of the conductive film is aligned with that of the conductive barrier film, and a width of the wiring containing Cu as its main component is narrower than that of the conductive barrier film.

5. (Previously Presented) A display device comprising:

at least a signal line and a scan line provided to intersect with the signal line,

wherein the scan line comprises a conductive barrier film and a wiring containing Cu as its main component over the conductive barrier film,

wherein a width of the wiring containing Cu as its main component is narrower than that of the conductive barrier film, and

wherein the width of the conductive barrier film is 30 to 40 μm and the width of the wiring containing Cu as its main component is 5 to 20 μm .

6. (Previously Presented) A display device comprising:

at least a signal line and a scan line provided to intersect with the signal line,

wherein the signal line comprises a conductive film, a first conductive barrier film on the conductive film, and a first wiring containing Cu as its main component over the first conductive barrier film,

wherein the scan line comprises a second conductive barrier film and a second

wiring containing Cu as its main component over the second conductive barrier film,
wherein a width of the conductive film is aligned with that of the first conductive barrier film, and a width of the first wiring containing Cu as its main component is narrower than that of the first conductive barrier film, and
wherein a width of the second wiring containing Cu as its main component is narrower than that of the second conductive barrier film.

7. (Previously Presented) A display device according to claim 4 further comprising a light emitting element, wherein driving current is supplied to the light emitting element through the signal line.

8. (Previously Presented) A display device according to claim 5 further comprising a light emitting element, wherein voltage is input to the light emitting element through the signal line.

9. (Previously Presented) A display device according to claim 6 further comprising a light emitting element, wherein voltage is input to the light emitting element through the signal line.

10. (Previously Presented) A display device according to claim 6 further comprising a light emitting element and a TFT electrically connected to the light emitting element, wherein a gate electrode of the TFT also comprises the second conductive barrier film and the second wiring containing Cu as its main component over the second conductive barrier film.

11. (Previously Presented) A display device according to claim 6 further comprising a light emitting element and a TFT electrically connected to the light emitting element, wherein source and drain electrodes of the TFT also comprises the conductive

film, the first conductive barrier film, and the first wiring containing Cu as its main component over the first conductive barrier film.

12. (Previously Presented) A semiconductor device comprising:
a semiconductor film over an insulating surface; and
a gate electrode over the semiconductor film,
wherein the gate electrode comprises a conductive barrier film and a wiring containing Cu as its main component over the conductive barrier film,
wherein a width of the wiring containing Cu as its main component is narrower than that of the conductive barrier film, and
wherein the width of the conductive barrier film is 30 to 40 μm and the width of the wiring containing Cu as its main component is 5 to 20 μm .

13. (Previously Presented) A semiconductor device comprising:
a semiconductor film over an insulating surface; and
a gate electrode over the semiconductor film,
wherein the gate electrode comprises a conductive film, a conductive barrier film on the conductive film, and a wiring containing Cu as its main component over the conductive barrier film,
wherein a width of the conductive barrier film is aligned with that of the conductive film, and
wherein a width of the wiring containing Cu as its main component is narrower than that of the conductive barrier film.

14. (Previously Presented) A semiconductor device comprising:
at least a wiring comprising a conductive film, a conductive barrier film on the conductive film, and a wiring containing Cu as its main component over the conductive barrier film; and

an input terminal electrically connected to the wiring,
wherein a width of the conductive wiring is aligned with that of the conductive barrier film,

wherein a width of the wiring containing Cu as its main component is narrower than that of the conductive barrier film, and

wherein the input terminal is not overlapped with the wiring containing Cu as its main component.

15. (Previously Presented) A semiconductor device according to claim 14, wherein the input terminal is connected to the wiring through resin comprising a conductor.

16. (Previously Presented) A semiconductor device according to claim 14, wherein an edge of the input terminal is not aligned with that of the wiring containing Cu as its main component.

17. (Previously Presented) A semiconductor device according to claim 14, wherein the wiring is connected to a protective circuit including a semiconductor film.

18. (Previously Presented) A semiconductor device according to claim 17 further comprising a scan line, wherein the scan line is also connected to the protective circuit.

19. (Previously Presented) A semiconductor device according to claim 1, wherein the conductive barrier film comprises at least one of TiN, TaN, TiC, TaC, and WN.

20. (Previously Presented) A semiconductor device according to claim 2,

wherein the conductive barrier film comprises at least one of TiN, TaN, TiC, TaC, and WN.

21. (Previously Presented) A semiconductor device according to claim 3, wherein the conductive barrier film comprises at least one of TiN, TaN, TiC, TaC, and WN.

22. (Original) A display device according to claim 4, wherein the conductive barrier film comprises at least one of TiN, TaN, TiC, TaC, and WN.

23. (Original) A display device according to claim 5, wherein the conductive barrier film comprises at least one of TiN, TaN, TiC, TaC, and WN.

24. (Original) A display device according to claim 6, wherein each of the first and second conductive barrier films comprises at least one of TiN, TaN, TiC, TaC, and WN.

25. (Previously Presented) A semiconductor device according to claim 12, wherein the conductive barrier film comprises at least one of TiN, TaN, TiC, TaC, and WN.

26. (Previously Presented) A semiconductor device according to claim 13, wherein the conductive barrier film comprises at least one of TiN, TaN, TiC, TaC, and WN.

27. (Previously Presented) A semiconductor device according to claim 14, wherein the conductive barrier film comprises at least one of TiN, TaN, TiC, TaC, and WN.

28. (Previously Presented) A semiconductor device according to claim 3, wherein the conductive film comprises Ti.

29. (Original) A display device according to claim 4, wherein the conductive film comprises Ti.

30. (Original) A display device according to claim 6, wherein the conductive film comprises Ti.

31. (Previously Presented) A semiconductor device according to claim 13, wherein the conductive film comprises Ti.

32. (Previously Presented) A semiconductor device according to claim 14, wherein the conductive film comprises Ti.

33. (Previously Presented) A semiconductor device according to claim 1, wherein the wiring containing Cu as its main component is covered with an insulating barrier film, and the insulating barrier film comprises at least one of silicon nitride, silicon oxynitride, and aluminum nitride.

34. (Previously Presented) A semiconductor device according to claim 2, wherein the insulating barrier film comprises at least one of silicon nitride, silicon oxynitride, and aluminum nitride.

35. (Previously Presented) A semiconductor device according to claim 3, wherein the wiring containing Cu as its main component is covered with an insulating barrier film, and the insulating barrier film comprises at least one of silicon nitride, silicon

oxynitride, and aluminum nitride.

36. (Original) A display device according to claim 4, wherein the wiring containing Cu as its main component is covered with an insulating barrier film, and the insulating barrier film comprises at least one of silicon nitride, silicon oxynitride, and aluminum nitride.

37. (Original) A display device according to claim 5, wherein the wiring containing Cu as its main component is covered with an insulating barrier film, and the insulating barrier film comprises at least one of silicon nitride, silicon oxynitride, and aluminum nitride.

38. (Original) A display device according to claim 6, wherein each of the first and second wiring is covered with an insulating barrier film, and the insulating barrier film comprises at least one of silicon nitride, silicon oxynitride, and aluminum nitride.

39. (Previously Presented) A semiconductor device according to claim 12, wherein the wiring containing Cu as its main component is covered with an insulating barrier film, and the insulating barrier film comprises at least one of silicon nitride, silicon oxynitride, and aluminum nitride.

40. (Previously Presented) A semiconductor device according to claim 13, wherein the wiring containing Cu as its main component is covered with an insulating barrier film, and the insulating barrier film comprises at least one of silicon nitride, silicon oxynitride, and aluminum nitride.

41. (Previously Presented) A semiconductor device according to claim 14, wherein the wiring containing Cu as its main component is covered with an insulating

barrier film, and the insulating barrier film comprises at least one of silicon nitride, silicon oxynitride, and aluminum nitride.

42.-49. (Canceled)

50. (Previously Presented) A semiconductor device comprising:
a conductive barrier film; and
a wiring containing Cu as its main component over the conductive barrier film,
wherein an edge of the conductive barrier film is not aligned with that of the
wiring containing Cu as its main component, and
wherein a width of the conductive barrier film is 30 to 40 μm and a width of the
wiring containing Cu as its main component is 5 to 20 μm .

51. (Previously Presented) A semiconductor device comprising:
a conductive film;
a conductive barrier film on the conductive film; and
a wiring containing Cu as its main component over the conductive barrier film,
wherein an edge of the conductive film is aligned with that of the conductive
barrier film, and
wherein an edge of the wiring containing Cu as its main component is not aligned
with that of the conductive barrier film.

52. (Previously Presented) A semiconductor device according to claim 50,
wherein the conductive barrier film comprises at least one of TiN, TaN, TiC, TaC, and
WN.

53. (Previously Presented) A semiconductor device according to claim 51,
wherein the conductive barrier film comprises at least one of TiN, TaN, TiC, TaC, and

WN.

54. (Previously Presented) A semiconductor device according to claim 51, wherein the conductive film comprises Ti.

55. (Previously Presented) A semiconductor device according to claim 50, wherein the wiring containing Cu as its main component is covered with an insulating barrier film, and the insulating barrier film comprises at least one of silicon nitride, silicon oxynitride, and aluminum nitride.

56. (Previously Presented) A semiconductor device according to claim 51, wherein the wiring containing Cu as its main component is covered with an insulating barrier film, and the insulating barrier film comprises at least one of silicon nitride, silicon oxynitride, and aluminum nitride.

57. (Currently Amended) A semiconductor device according to claim 1, wherein the ~~display~~ semiconductor device is incorporated in an electronic device selected from the group consisting of a large-sized display device, a lap-top computer, a portable image reproduction device including a recording medium and a portable information terminal.

58. (Currently Amended) A semiconductor device according to claim 2, wherein the ~~display~~ semiconductor device is incorporated in an electronic device selected from the group consisting of a large-sized display device, a lap-top computer, a portable image reproduction device including a recording medium and a portable information terminal.

59. (Currently Amended) A semiconductor device according to claim 3, wherein

the display semiconductor device is incorporated in an electronic device selected from the group consisting of a large-sized display device, a lap-top computer, a portable image reproduction device including a recording medium and a portable information terminal.

60. (Previously Presented) A display device according to claim 4, wherein the display device is incorporated in an electronic device selected from the group consisting of a large-sized display device, a lap-top computer, a portable image reproduction device including a recording medium and a portable information terminal.

61. (Previously Presented) A display device according to claim 5, wherein the display device is incorporated in an electronic device selected from the group consisting of a large-sized display device, a lap-top computer, a portable image reproduction device including a recording medium and a portable information terminal.

62. (Previously Presented) A display device according to claim 6, wherein the display device is incorporated in an electronic device selected from the group consisting of a large-sized display device, a lap-top computer, a portable image reproduction device including a recording medium and a portable information terminal.

63. (Currently Amended) A semiconductor device according to claim 12, wherein the display semiconductor device is incorporated in an electronic device selected from the group consisting of a large-sized display device, a lap-top computer, a portable image reproduction device including a recording medium and a portable information terminal.

64. (Currently Amended) A semiconductor device according to claim 13, wherein the display semiconductor device is incorporated in an electronic device

selected from the group consisting of a large-sized display device, a lap-top computer, a portable image reproduction device including a recording medium and a portable information terminal.

65. (Currently Amended) A semiconductor device according to claim 14, wherein the ~~display~~ semiconductor device is incorporated in an electronic device selected from the group consisting of a large-sized display device, a lap-top computer, a portable image reproduction device including a recording medium and a portable information terminal.

66. (Currently Amended) A semiconductor device according to claim 50, wherein the ~~display~~ semiconductor device is incorporated in an electronic device selected from the group consisting of a large-sized display device, a lap-top computer, a portable image reproduction device including a recording medium and a portable information terminal.

67. (Currently Amended) A semiconductor device according to claim 51, wherein the ~~display~~ semiconductor device is incorporated in an electronic device selected from the group consisting of a large-sized display device, a lap-top computer, a portable image reproduction device including a recording medium and a portable information terminal.